



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _A = +25°C
-30V	$32m\Omega$ @ V _{GS} = -10V	-5.8A
-307	$50m\Omega$ @ V _{GS} = -4.5V	-4.6A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Backlighting

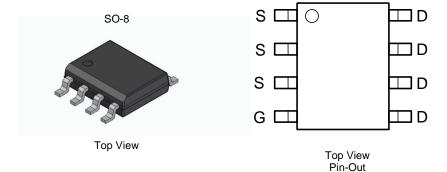
Features

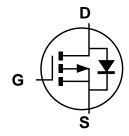
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP3037LSSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)





Equivalent Circuit

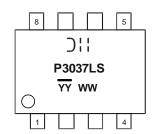
Ordering Information (Note 4)

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Part Number	Case	Packaging
DMP3037LSSQ-13	SO-8	2500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking P3037LS = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

December 2019

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	-30	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6) Vgs = -10V	$T_A = +25$ °C $T_A = +70$ °C	lo	-5.8 -4.6	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-40	Α	
Avalanche Current (Note 7) L = 0.1mH		las	-17	Α
Avalanche Energy (Note 7) L = 0.1mH		Eas	15	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	D-	1.2	W
	T _A = +70°C	Pb	0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	100	°C/W
	t<10s	КӨЈА	58	
Total Dawer Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	1.6	W
Total Power Dissipation (Note 6)	T _A = +70°C	Pb	1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	77	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	КӨЈА	45	
Thermal Resistance, Junction to Case (Note 6)		Rejc	10	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

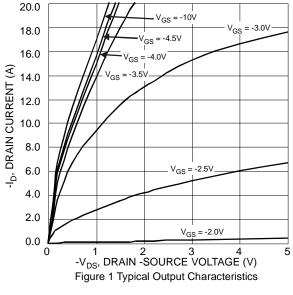
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

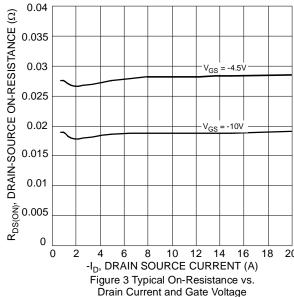
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_	_	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(th)	-1.0	_	-2.4	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Descour		19	32	mΩ	$V_{GS} = -10V, I_{D} = -6A$	
Static Drain-Source On-Resistance	RDS(ON)	_	28	50	11122	$V_{GS} = -4.5V, I_{D} = -5A$	
Diode Forward Voltage	V _{SD}	_	-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	1	969	_	pF	\\ 45\\\\\ 0\\	
Output Capacitance	Coss	I	138	_	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	1	102	_	pF	1 = 1.0IVII 12	
Gate Resistance	Rg	_	13	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -10V)	Qg	_	17.3	_	nC	V _{DS} = -15V, I _D = -7A	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	8.2	_	nC		
Gate-Source Charge	Qgs	_	2.5	_	nC	V _{DS} = -15V, I _D = -7A	
Gate-Drain Charge	Q_{gd}	_	2.8	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.7	_	ns		
Turn-On Rise Time	t _R		5	_	ns	$V_{DS} = -15V$, $V_{GS} = -10V$, $R_{L} = 2.15\Omega$, $R_{GEN} = 3\Omega$	
Turn-Off Delay Time	tD(OFF)		43	_	ns		
Turn-Off Fall Time	tF	_	20	_	ns		
Body Diode Reverse Recovery Time	trr	_	13.6	_	ns	Is = -7A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	1	3.4	_	nC	I _S = -7A, dI/dt = 100A/μs	

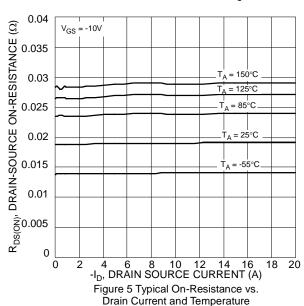
Notes:

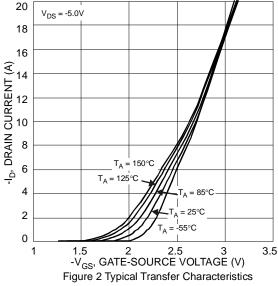
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

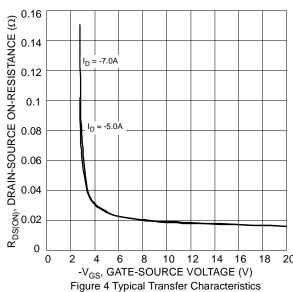












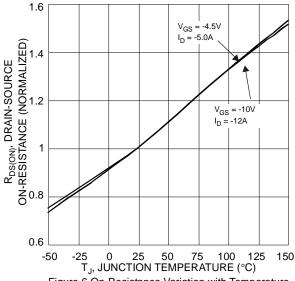
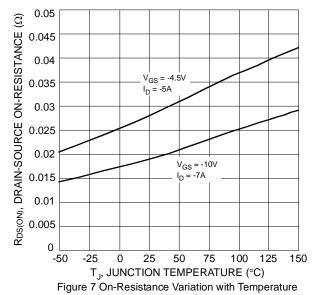


Figure 6 On-Resistance Variation with Temperature





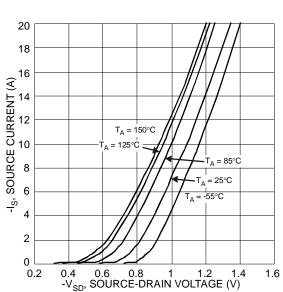
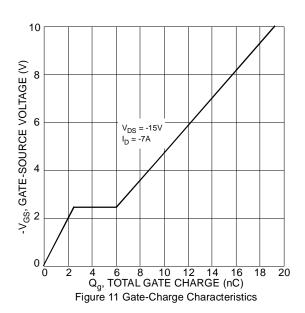
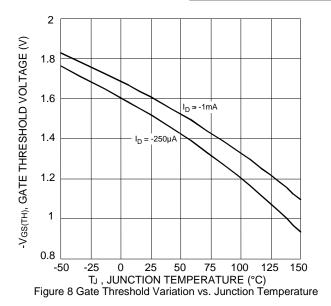
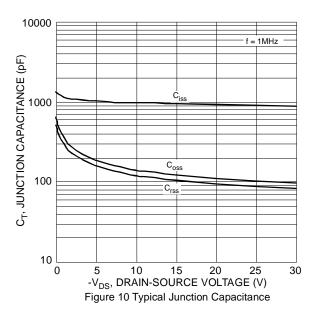
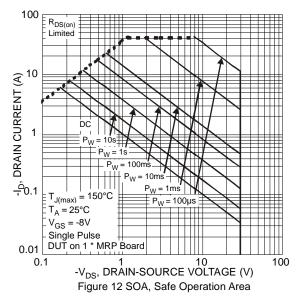


Figure 9 Diode Forward Voltage vs. Current

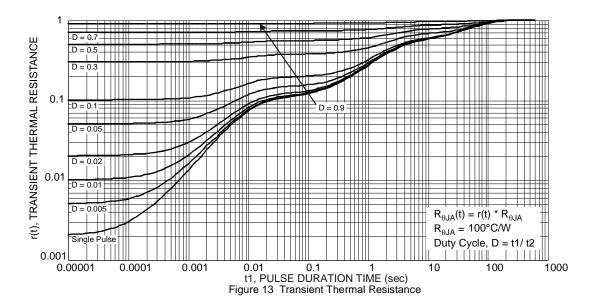








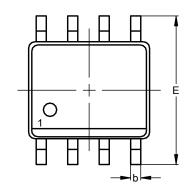


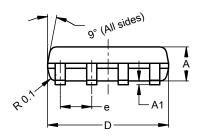


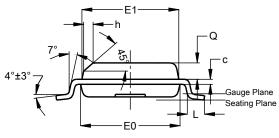


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.







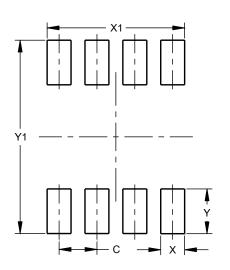
SO-8

SO-8

SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
Y1	6.50



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